

Number	Hits	Search Text	IP	Time Stamp
1	2072	"low-k" or dielectric or insulating and resist or photoresist or pattern or patterning or patterned and trench or via or contact or openings and etch\$3	USPAT; EPO; JPO; IBM_TDB	2003/04/01 19:32
3	1-14	"dual damascene" or dual adj damascene	USPAT; EPO; JPO; IBM_TDB	2003/04/01 19:37
4	1482	"low-k" or dielectric or insulating and resist or photoresist or pattern or patterning or patterned and trench or via or contact or openings and etch\$3 and "dual damascene" or dual adj damascene	USPAT; EPO; JPO; IBM_TDB	2003/04/01 19:57
5	14	ash or ashing or ashed and "in-situ" and etch\$3 and "low-k"	USPAT; EPO; JPO; IBM_TDB	2003/04/01 09:17
6	21	"low-k" or dielectric or insulating and resist or photoresist or pattern or patterning or patterned and trench or via or contact or openings and etch\$3 and "organo silicate glass" or OSG	USPAT; EPO; JPO; IBM_TDB	2003/04/01 09:14
7	231	ash or ashing or ashed same "water vapor" or "H.sub.2O" same oxygen or "O.sub.2"	USPAT; EPO; JPO; IBM_TDB	2003/04/01 09:33
7	29	ash or ashing or ashed same "water vapor" or "H.sub.2O" same oxygen or "O.sub.2" and "low-k" or dielectric or insulating and resist or photoresist or pattern or patterning or patterned and trench or via or contact or openings and etch\$3	USPAT; EPO; JPO; IBM_TDB	2003/04/01 07:39
9	1	43*0096.pn.	USPAT; EPO; JPO; IBM_TDB	2003/04/01 07:13
11	58	dielectric same "organo silicate glass" or OSG or "black diamond"	USPAT; EPO; JPO; IBM_TDB	2003/04/01 08:17
14	76	dielectric and "organo silicate glass" or OSG or "black diamond"	USPAT; EPO; JPO; IBM_TDB	2003/04/01 08:25
15	24	dielectric and "organo silicate glass" or OSG	USPAT; EPO; JPO; IBM_TDB	2003/04/01 08:47
17	173	"dielectric constant" and "organo silicate glass" or OSG	USPAT; EPO; JPO; IBM_TDB	2003/04/01 09:17
24	3149	"low-k" or dielectric or insulating and resist or photoresist or pattern or patterning or patterned and trench or via or contact or openings and etch\$3 and ash or ashing or ashed	USPAT; EPO; JPO; IBM_TDB	2003/04/01 09:32
25	1-14	"low-k" or dielectric or insulating and resist or photoresist or pattern or patterning or patterned and trench or via or contact or openings and etch\$3 and ash or ashing or ashed and 43*0096.pn.	USPAT; EPO; JPO; IBM_TDB	2003/04/01 09:32
26	142	"low-k" or dielectric or insulating and resist or photoresist or pattern or patterning or patterned and trench or via or contact or openings and etch\$3 and ash or ashing or ashed and 43*0096.pn. and "water vapor" or "H.sub.2O" and oxygen or "O.sub.2"	USPAT; EPO; JPO; IBM_TDB	2003/04/01 09:32

SEARCH HISTORY 411 11:00:01 AM 10/10/03

1: APT EAST W 100 1000 1000 1000